

# isc N-Channel MOSFET Transistor

# IPD65R600E6,IIPD65R600E6

#### • FEATURES

- Static drain-source on-resistance: R<sub>DS</sub>(on)≤0.6Ω
- Enhancement mode:
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

- · Fast switching
- · Very high commutation ruggedness

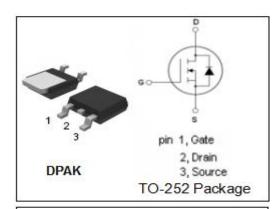


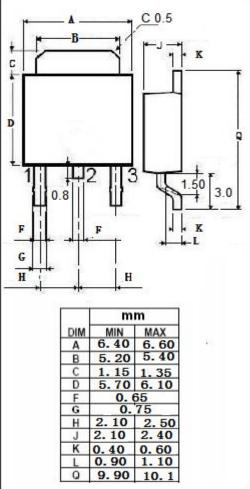
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL            | PARAMETER                              | VALUE   | UNIT       |  |
|-------------------|--|---------|------------|--|
| $V_{	extsf{DSS}}$ | Drain-Source Voltage                   | 650     | V          |  |
| V <sub>GS</sub>   | Gate-Source Voltage                    | ±20     | V          |  |
| l <sub>D</sub>    | Drain Current-Continuous               | 7.3     | Α          |  |
| I <sub>DM</sub>   | Drain Current-Single Pulsed            | 18      | Α          |  |
| $P_D$             | Total Dissipation @T <sub>C</sub> =25℃ | 63      | W          |  |
| Tj                | Max. Operating Junction Temperature    | 150     | °C         |  |
| T <sub>stg</sub>  | Storage Temperature                    | -55~150 | $^{\circ}$ |  |

### • THERMAL CHARACTERISTICS

| SYMBOL   | PARAMETER                             | MAX | UNIT |  |
|----------|---------------------------------------|-----|------|--|
| Rth(j-c) | Channel-to-case thermal resistance    |     | °C/W |  |
| Rth(j-a) | Channel-to-ambient thermal resistance | 62  | °C/W |  |







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS  | MIN | ТҮР | MAX | UNIT       |
|---------------------|--------------------------------|---|-----|-----|-----|------------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =1mA                  | 650 |     |     | V          |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.21mA | 2.5 |     | 3.5 | V          |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =2.1A                |     |     | 0.6 | Ω          |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> =20V; V <sub>DS</sub> =0V                 |     |     | 0.1 | μ <b>А</b> |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =650V; V <sub>GS</sub> = 0V               |     |     | 1   | μА         |
| V <sub>SD</sub>     | Diode forward voltage          | I <sub>F</sub> =3.2A, V <sub>GS</sub> = 0V                |     | 0.9 |     | V          |

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